

mfSANSの夜明け

—小型集束型中性子小角散乱装置—

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プロジェクトメンバー

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- 鬼柳善明、加美山隆
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- 京大原子炉実験所：杉山正明, 日野正裕
- 東大物性研：柴山充弘、吉澤秀樹
- 高エネ機構物構研中性子：瀬戸秀紀、清水裕彦、山田悟史、佐藤節夫
- 三重大学: 鳥飼直也
- 理研：広田克也
- 東大院工：高橋浩之、藤原健
- 日本原子力研究開発機構：遠藤仁
-

Long time project

圧倒的に多くの人に 中性子を

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ただ幾つかの装置を開発しているのでは
ありません。

X-ray SAS instrument

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実験室 X線装置
(小角散乱装置)



何時でも出来る
どこにも有る

例えばSAXS

http://matrix-dev.ansto.gov.au/research/bragg_institute/facilities/instruments/saxs/mimi_saxs

放射光施設
ヨーロッパ共同



非常に強力

例えばESRF、SPRING-8、PF

<http://www.lightsources.org/cms/?pid=1000103>

Neutron SAS instrument

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実験室 中性子装置
(小角散乱装置)



何時でも使える。
どこにでも有る

巨大中性子施設



例えばJ-PARC, JRR-3, ILL,
SNS, etc.

非常に強力

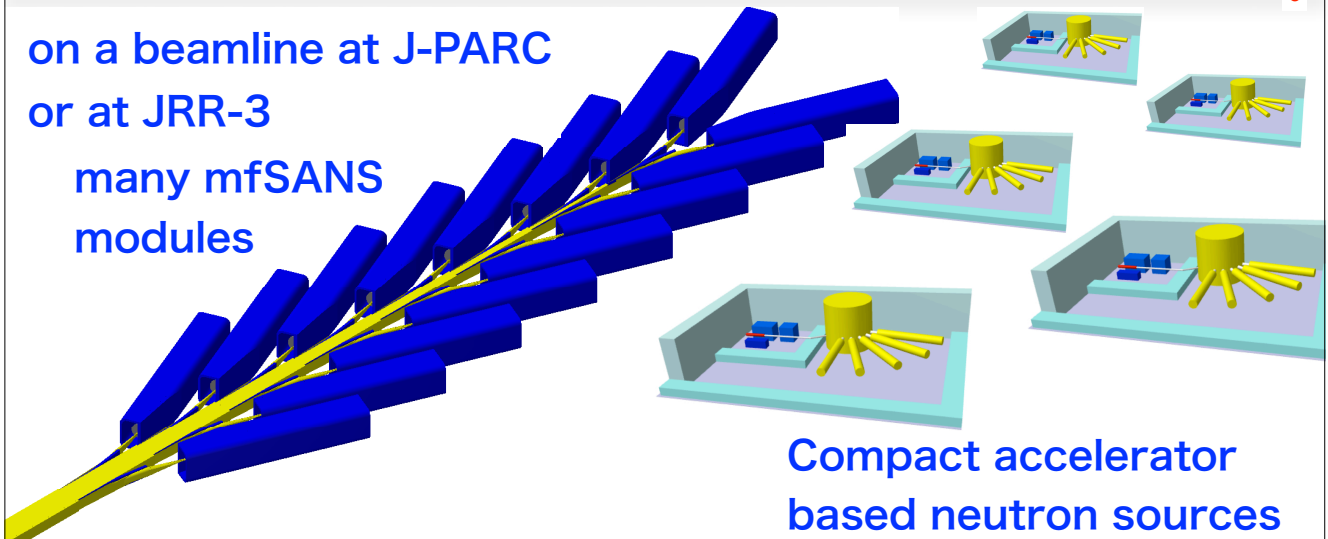
沢山の

小型集束型小角散乱装置を

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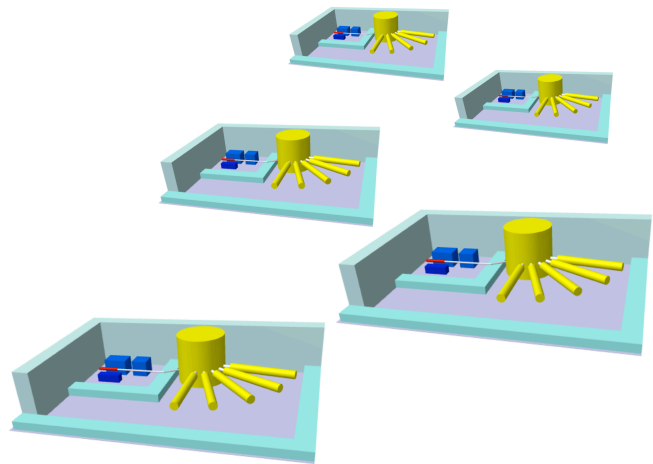
on a beamline at J-PARC
or at JRR-3

many mfSANS
modules



Compact accelerator based pulsed cold neutron source

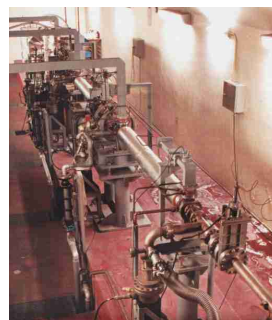
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Accelerator-driven laboratory-size neutron-source

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- RFQ accelerator + DTL $\approx 3-11$ MeV
 - Li or Be target
- Combined with:
 - many mfSANS modules,
 - mini-reflectometers,
 - mini-powder machines??



Hokkaido Univ.
Electron linac + mfSANS



LENS @ Indiana Univ.
<http://www.iucf.indiana.edu/lens/>

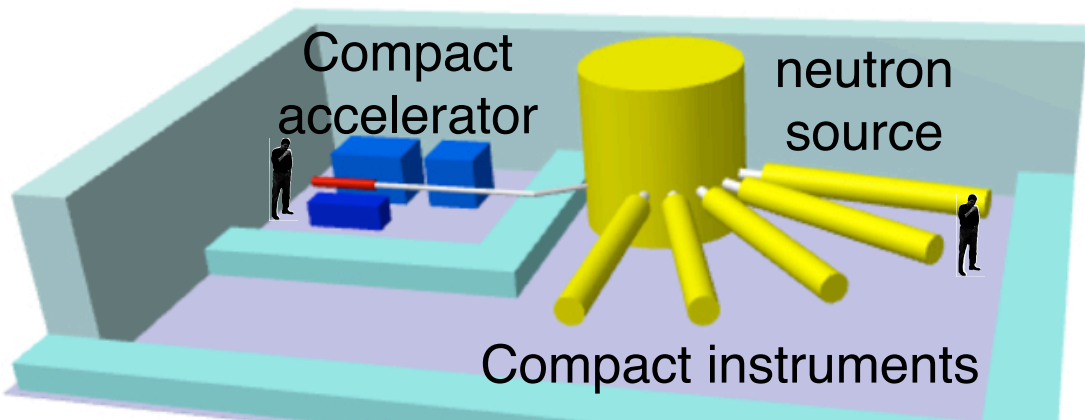
- CPHS@Tsinghua Univ. China
 - under construction
- proton linac@Kyoto Univ.
 - under construction

Conceptual design of a compact accelerator

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- Compact accelerator/
 - pulsed cold neutron source
 - instruments
- Electron accelerator of ~40-60 MeV, 3-10 kW
 - Cf. HU Linac: 35 MeV, 1 kW

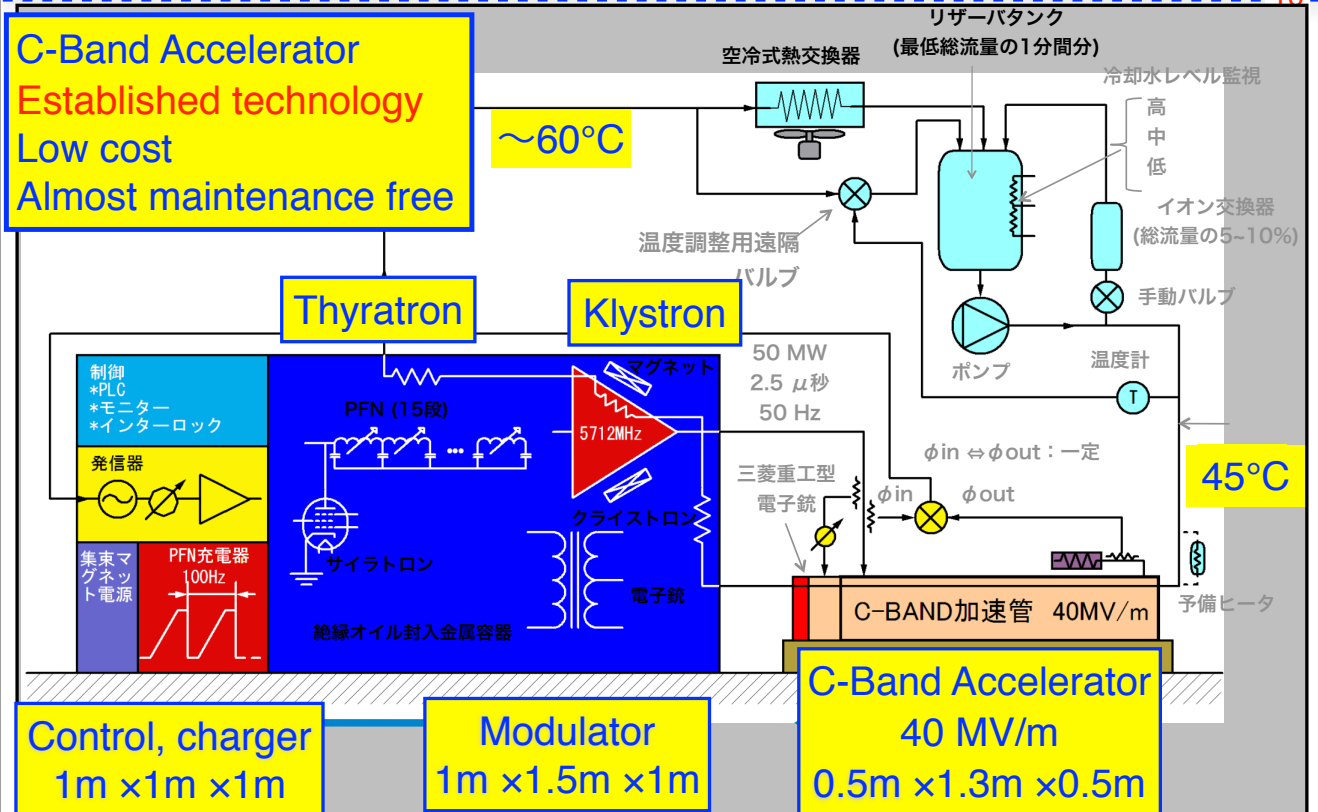
Collaboration with KEK accelerator people



Accelerator conceptual design

Kobayashi, Yoshioka, Matsumoto@kek

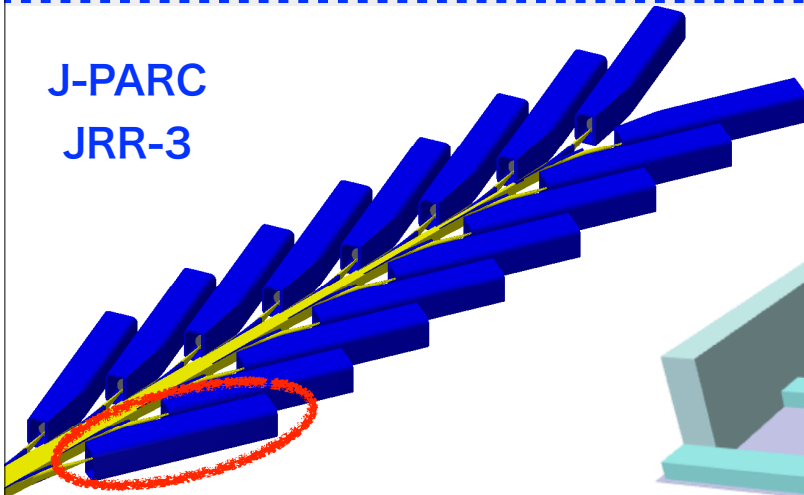
10



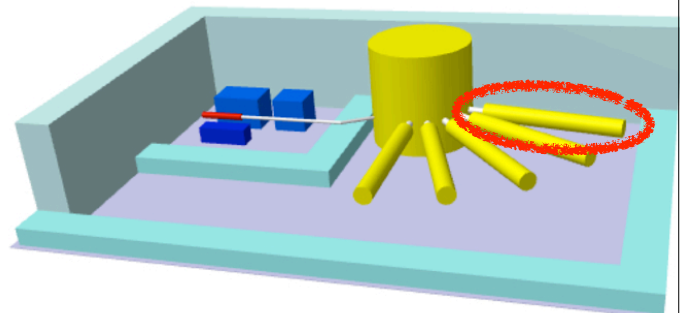
モジュールとしての 小型集束型中性子小角散乱装置 mfSANSの開発

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J-PARC
JRR-3



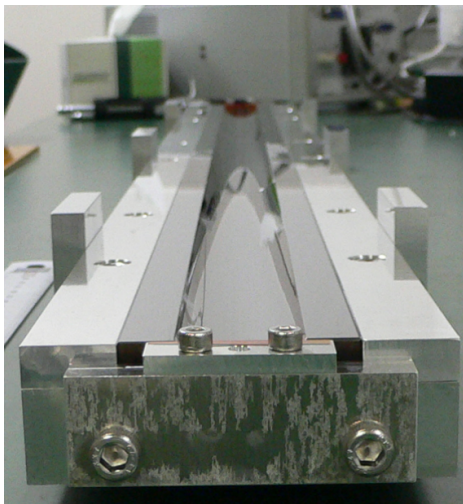
小型加速器
中性子源



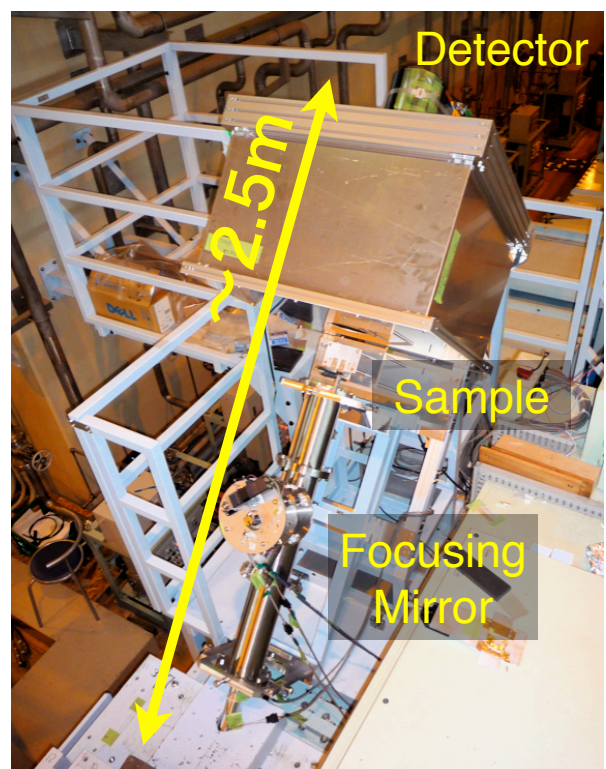
Mini-focusing SANS @ JRR-3 using a focusing mirror

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- Ellipsoidal mirror
 - 2.5 Q_c supermirror
 - 2.5 m between focal points
 - short radius 20 mm



L: 900mm
W: 20mm

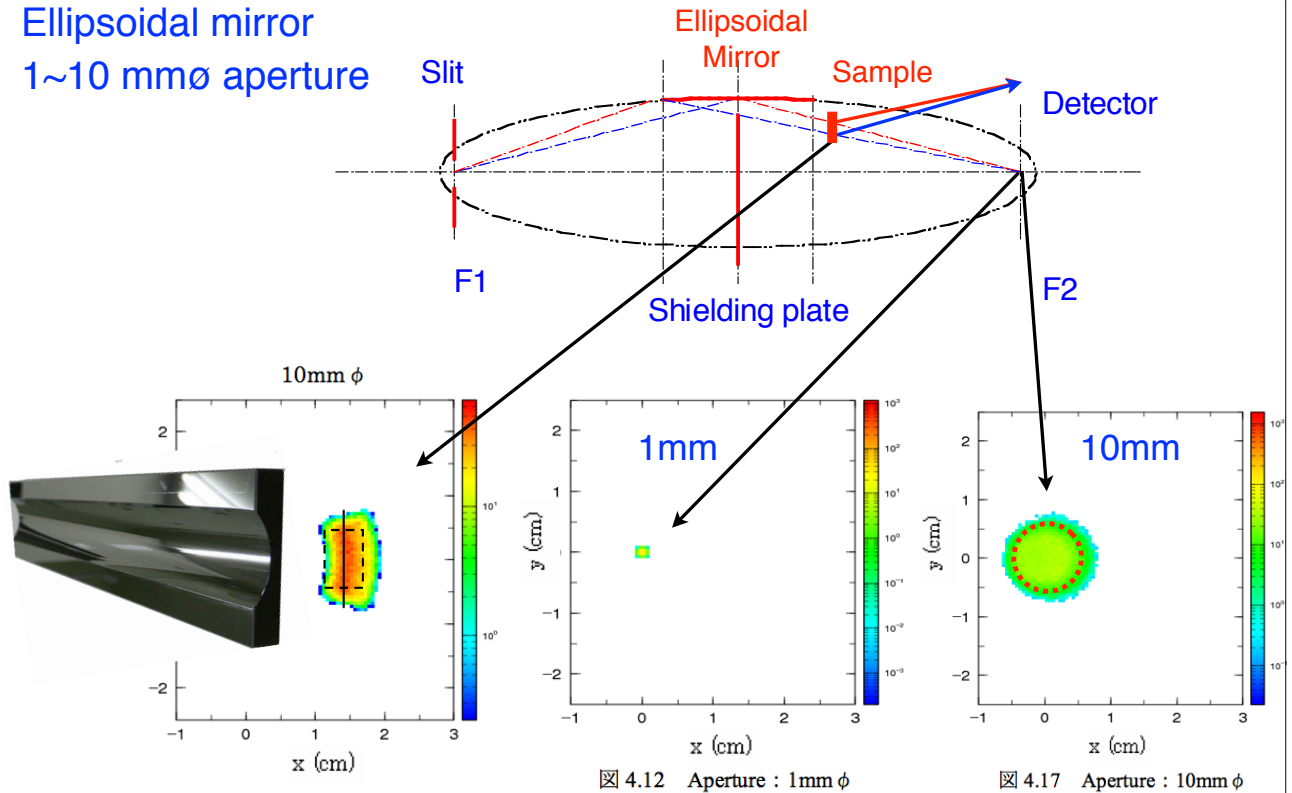


Ellipsoidal mirror focusing SANS

Kamada et al. (Hokkaido Univ.)

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- Ellipsoidal mirror
- 1~10 mm ϕ aperture

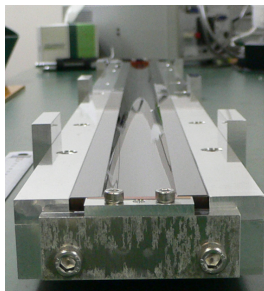


苦勞してます-1

Adjusting mirror-misalignment

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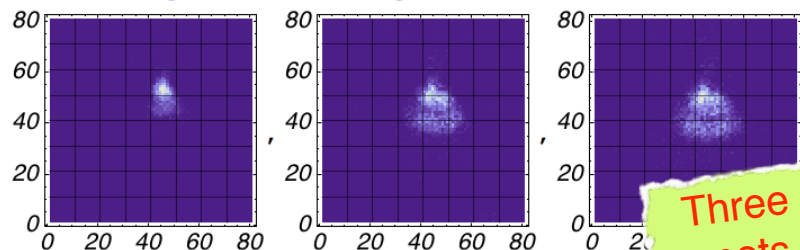
- The mirror is made of 3 pieces



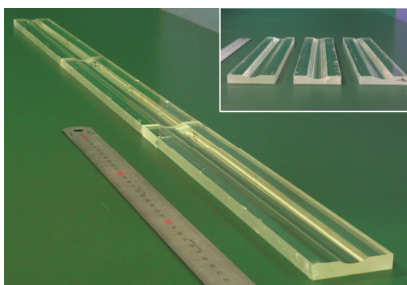
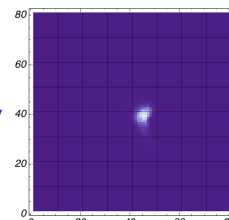
Alignment:

- Alignment in a few 10s of μm
- Dusts really affect
- Very fine mechanical

Aperture alignment matters.



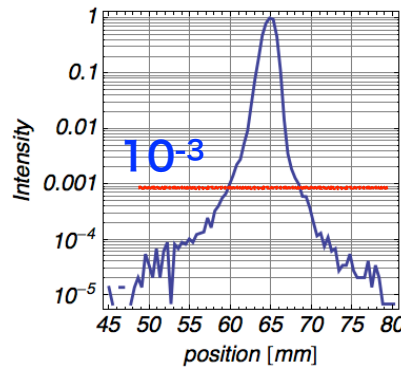
Eventually



The mirror is not perfect, but OK.

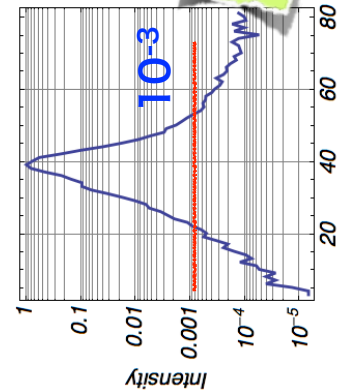
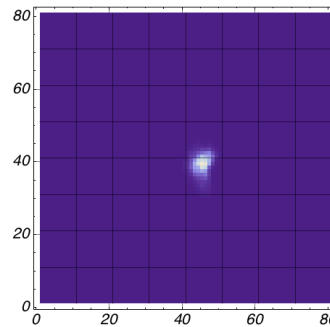
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- Beam broadening starts at around 1/1000 of the peak.
- Grinder mesh was #1200 where #8000 was required.
- New mirror has already been made, but...
 - #8000 finished
 - not coated yet



FWHM ≈ 2.5 mm
with 2 mm aperture

Surface roughness

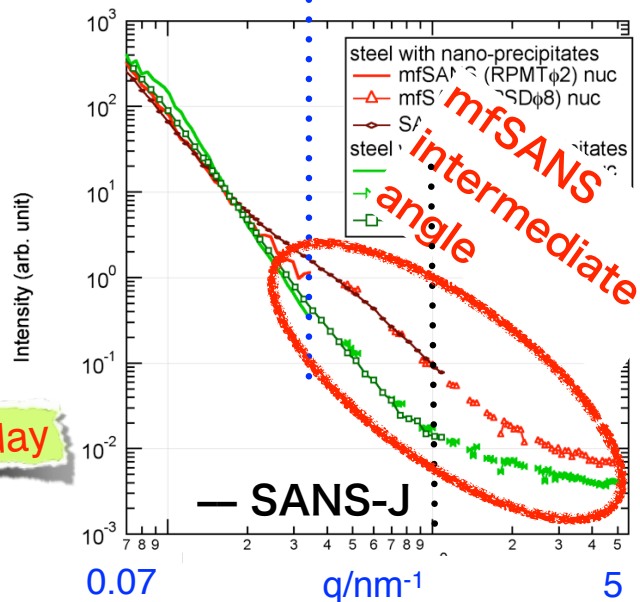


Nano-precipitates in Steel

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- Nano-size inhomogeneities

— mfSANS
— Low Angle bank



Nearly 1 day

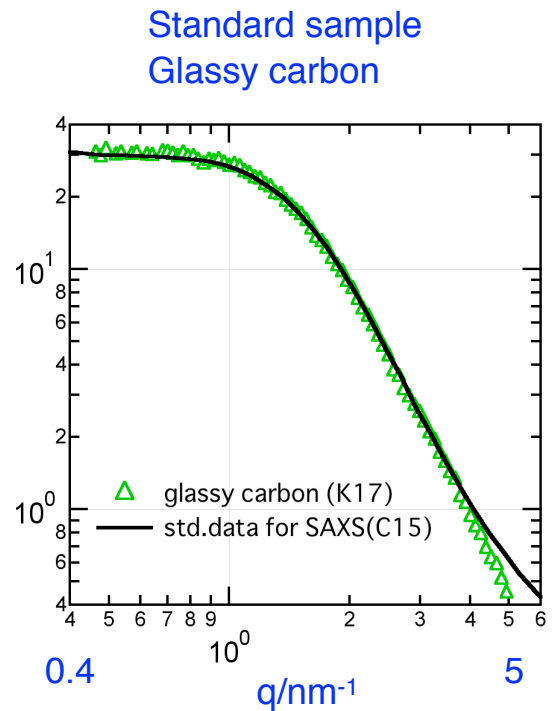
wider-angle scattering

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- 48 Linear position sensitive detectors at higher angle pos.
 - 1/2 inch dia, 600 mm in length
 - GE made



Intensity (arb. unit)



focusing SANS for low power reactors

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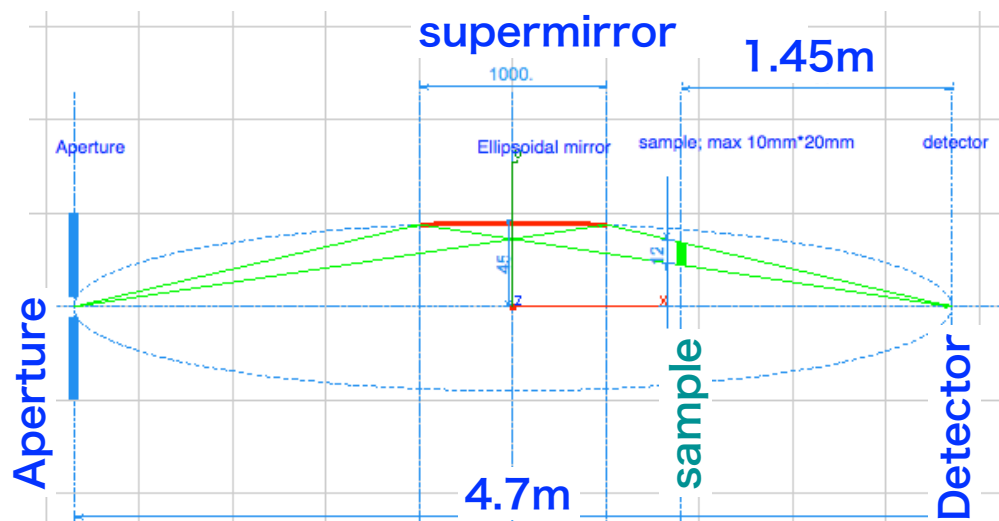
KUR version of focusing SANS

First Draft design

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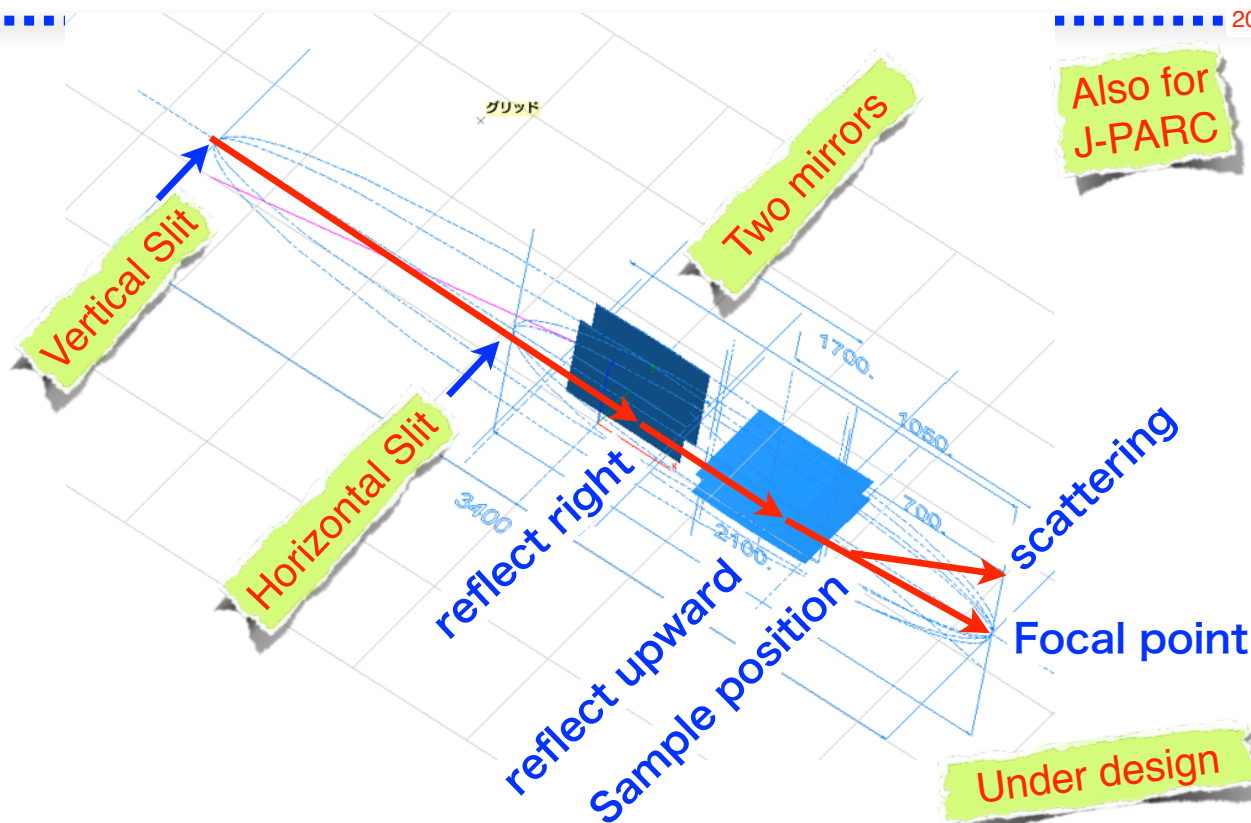
- boundary conditions:
 - 1MW thermal, use 2.7 A
 - Ni guide exit
 - Aim at $Q_{\min} \leq 0.01 \text{ \AA}^{-1}$
 - Use 5 mm resolution detector
 - 4.7m limit

Ellipsoidal mirror
4Qc; 1 m
Monochromating
supermirror



Kirpatrick-Baez mirror focusing SANS

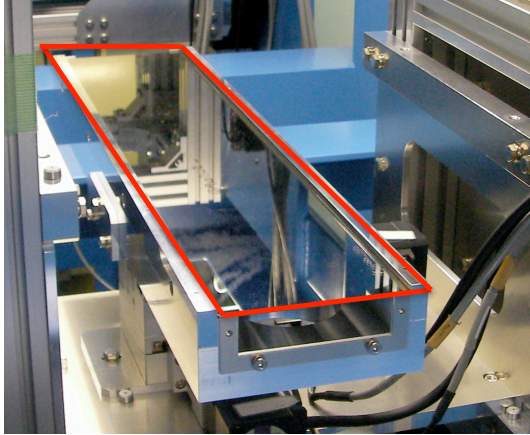
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Focusing by a bent supermirror

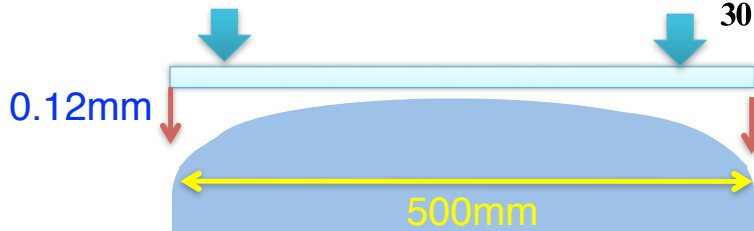
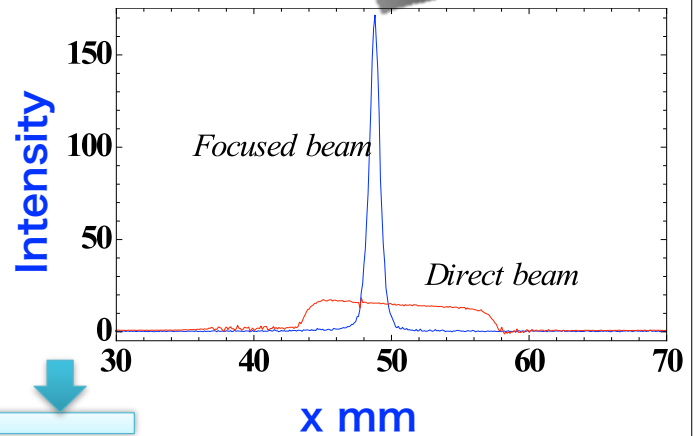
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- Bent gently
- Only a slight bending $\approx 120\mu\text{m}$



For reflectometer
& K-B mirror type SANS

1 mm focusing

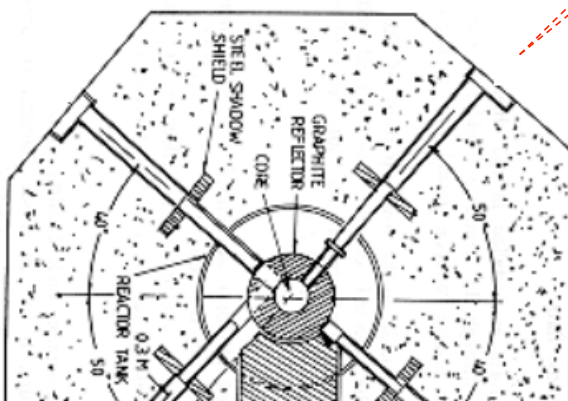
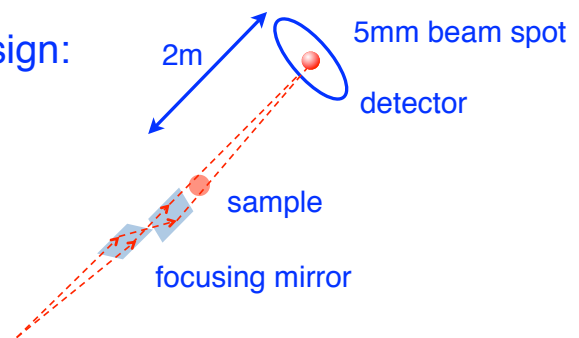


N. Yamada@kek, N.Torikai@Mie Univ.
T. Sugita@Hokkaido Univ.

Reaktor TRIGA PUSPATI (RTP), Malaysia

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- 1 MW TRIGA reactor
- No cold source
- Radial beam port
- Focusing SANS instrument under design:
 - $\approx 10^4$ n/s @ 4.5 A estimated
 - Reasonable Q-range with 5mm beam spot



By Megat Harun modified by M.F.

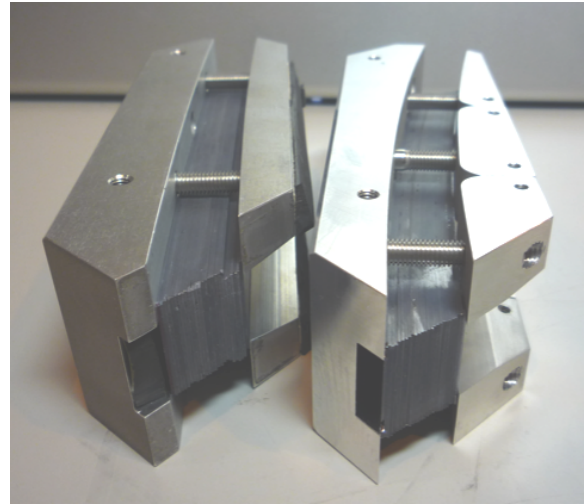
ビーム分岐

苦労しています。

準モノクロメータ開発

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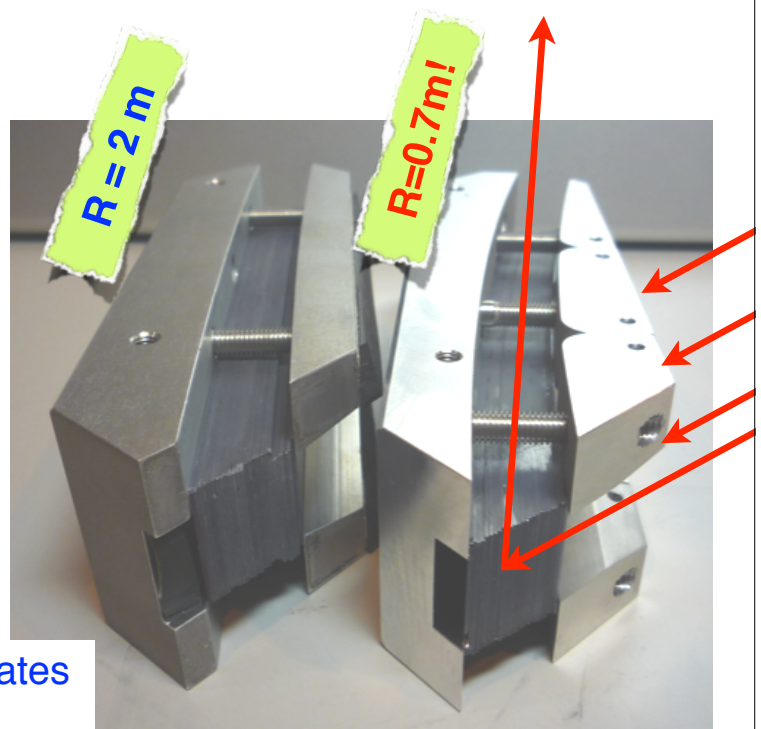
- 原子炉で装置をたくさん並べる
- 分岐が必要



Strongly bent perfect Si crystal plates

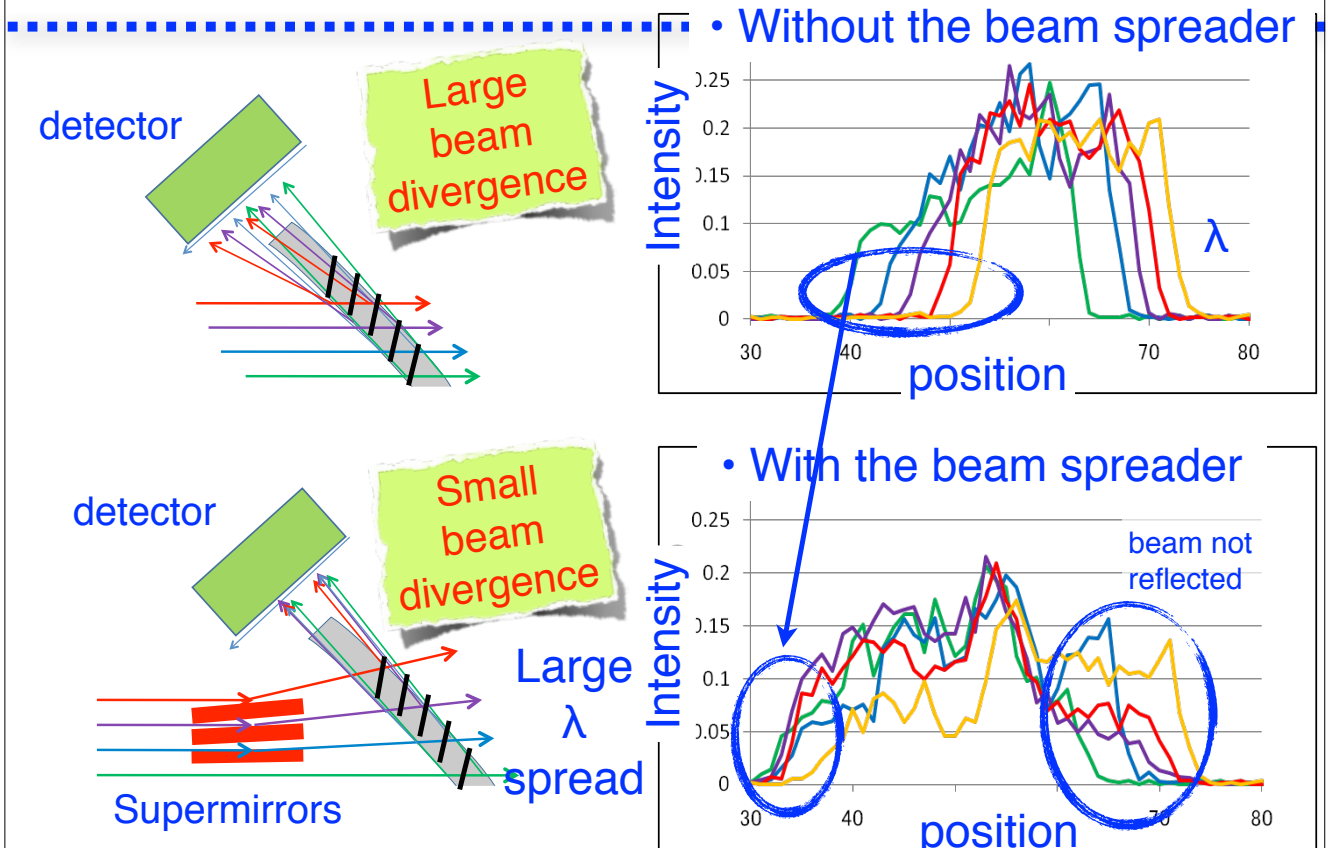
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- Fully asymmetric geometry
 - 5.8 A
 - 0.5 mm thick Si plates x 30 plates
 - Brighter than a PG monochromator



0.5 mm thick Si plates
x 30 plates

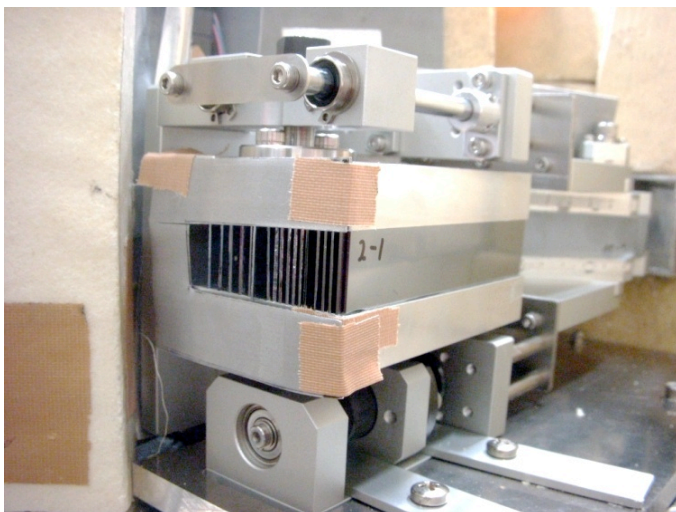
With and without the beam spreader



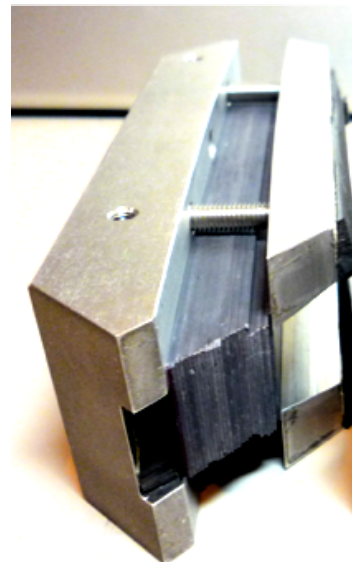
Monochromator with a beam spreader

Bent $R=2m$

Beam spreader with 2.2 & 4.4 Q_c supermirrors



Strongly bent perfect Si crystal plates, $R=2m$

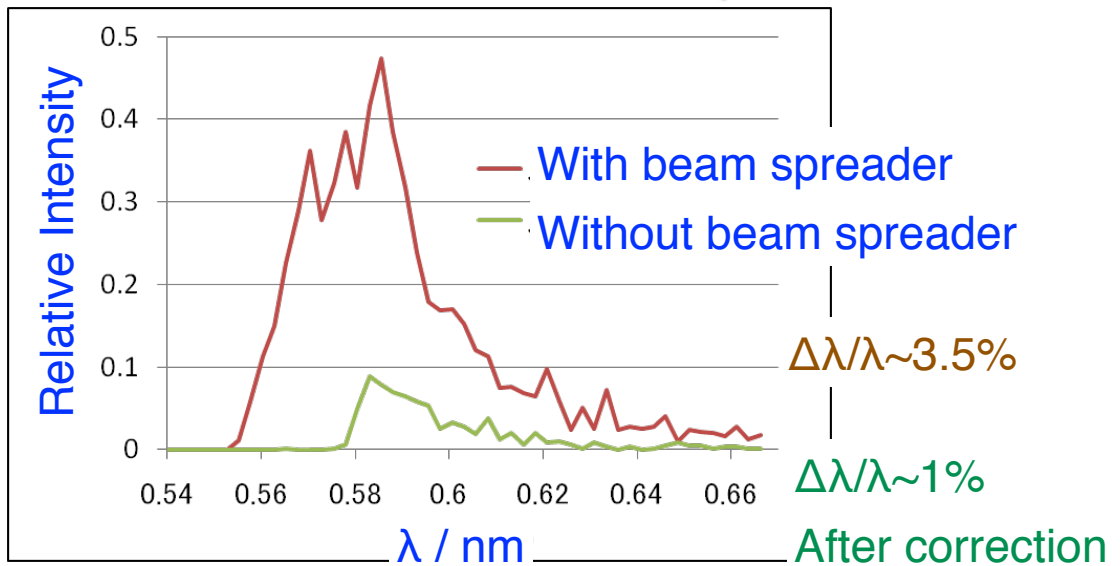


バンド幅はOKしかし、 $R \approx 0.7m$ が必要

Bent $R=2m$

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- Estimated beam intensity at the mirror

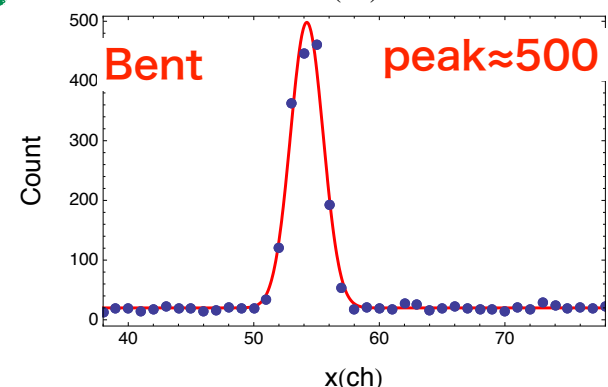
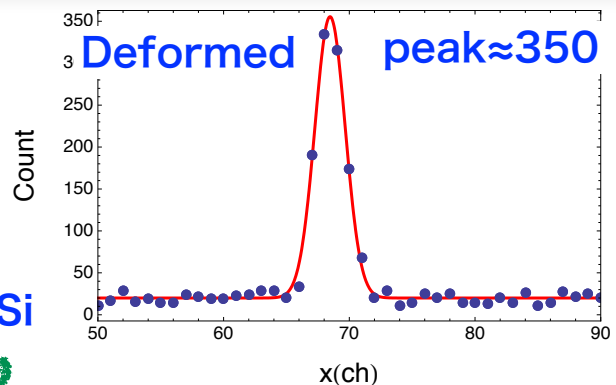
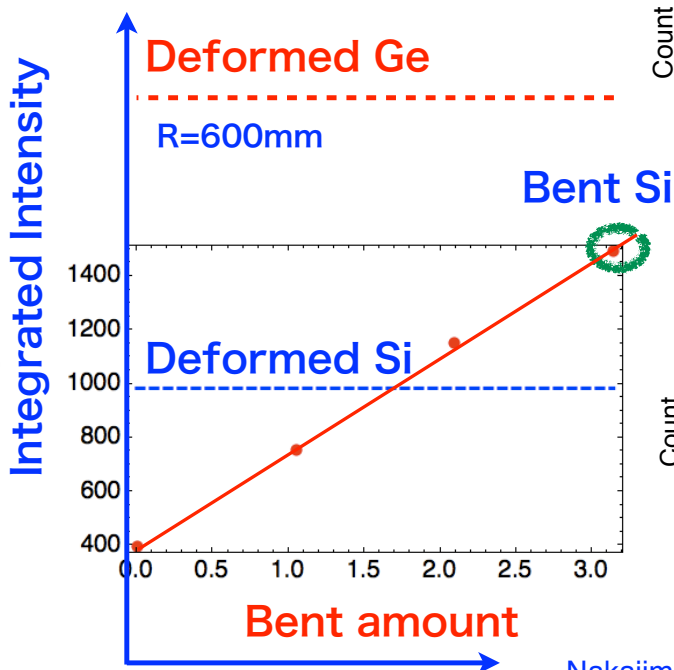


- ~ 8 times intense?

Deformed Si/Ge & Bent Si

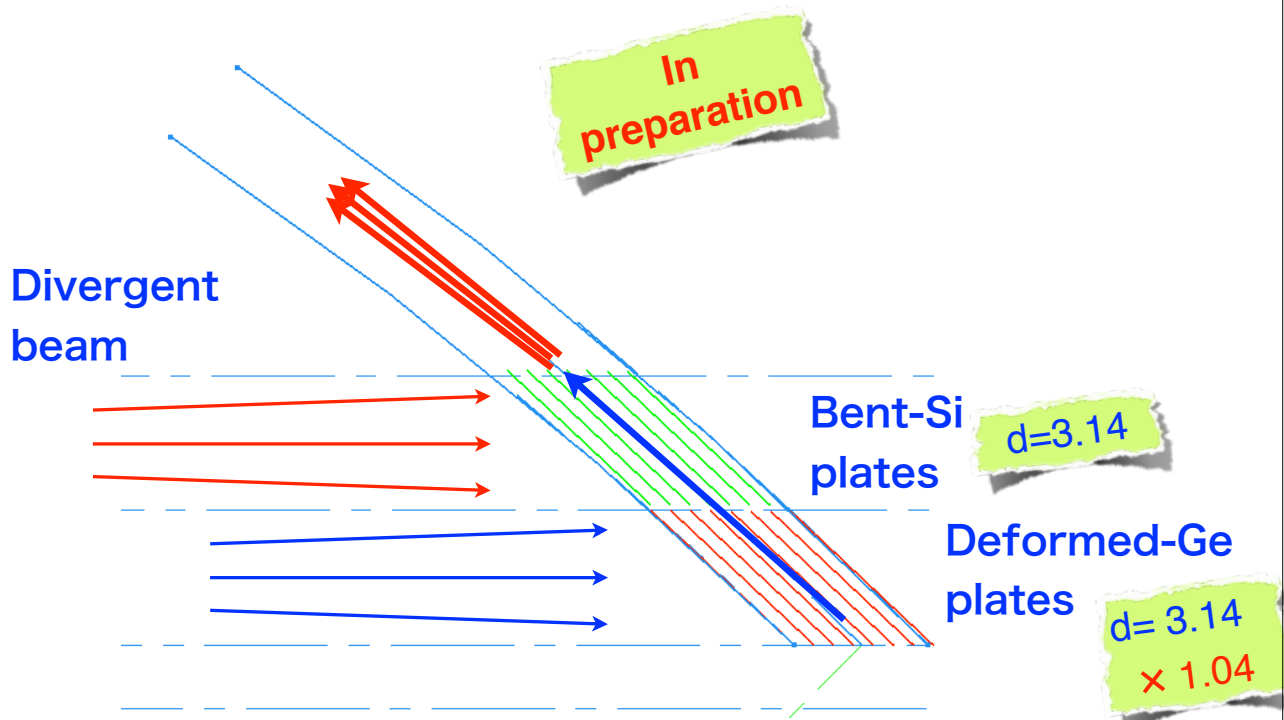
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- Si/Geを高温高圧で変形



Bent-Si/Deformed-Ge monochromator

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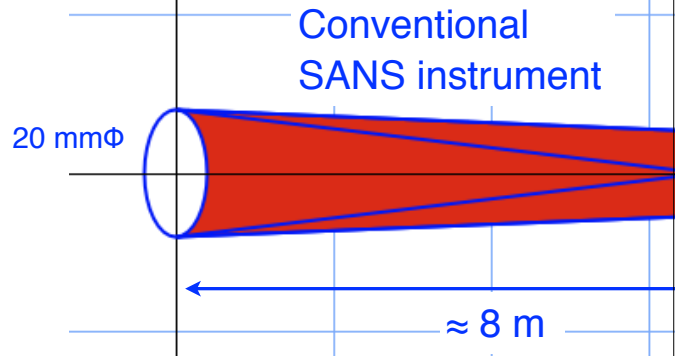
Multi-pinhole scanning SANS

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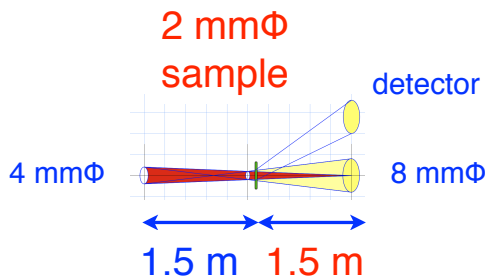
小さなピンホールでの中性子小角散乱

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- ピンホール $\approx 2 \text{ mm } \phi$
- 試料も $2 \text{ mm } \phi$
- 強度は落ちる
- マルチピンホールで強度を稼ぐ



$$I(Q) \propto \phi \cdot d\Omega_i \cdot \frac{d\Sigma}{d\Omega} \cdot V_{\text{sample}} \cdot \eta \cdot d\Omega_f$$

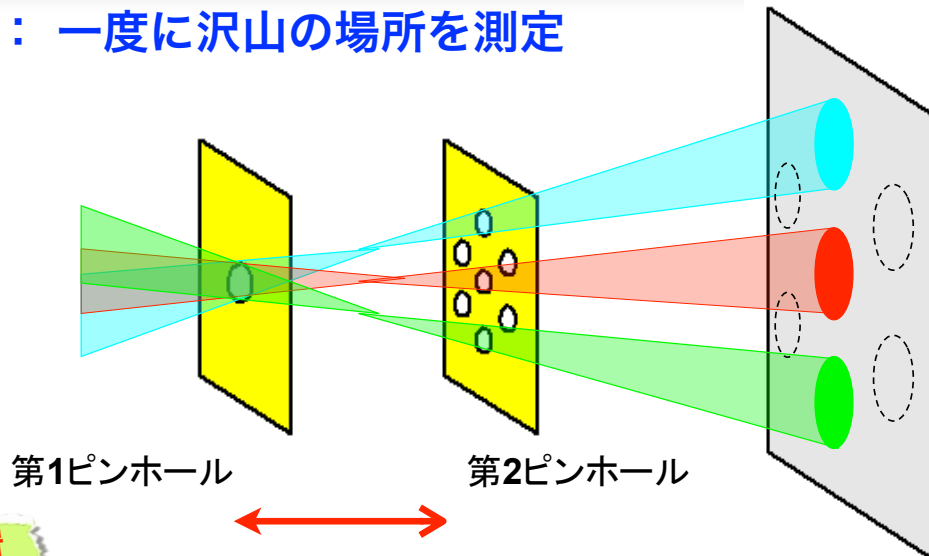


Q分解能は同じ、
強度は落ちる
→マルチピンホール

Multi-pinhole SANS

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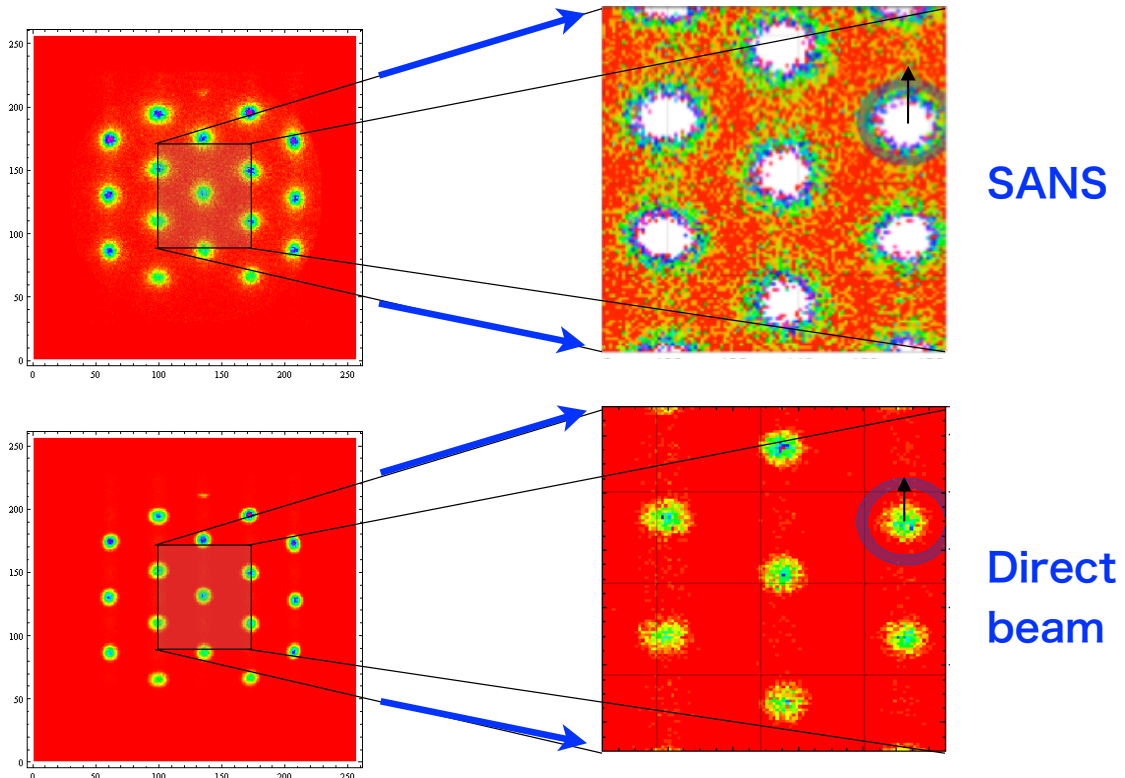
- Scanning : 一度に沢山の場所を測定



または逆転配置

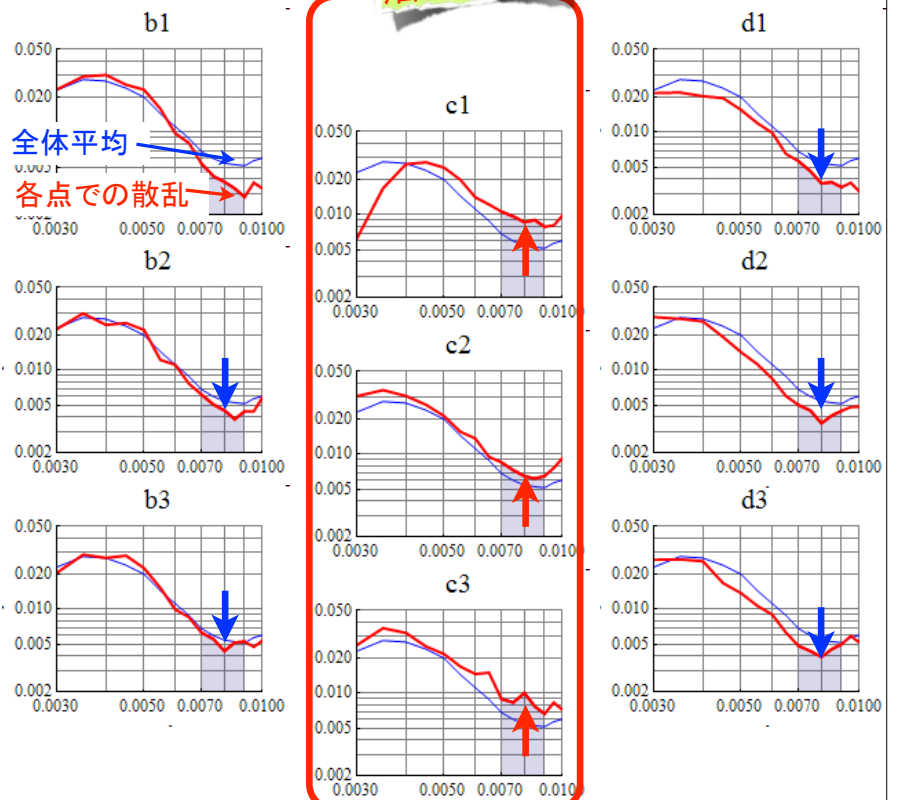
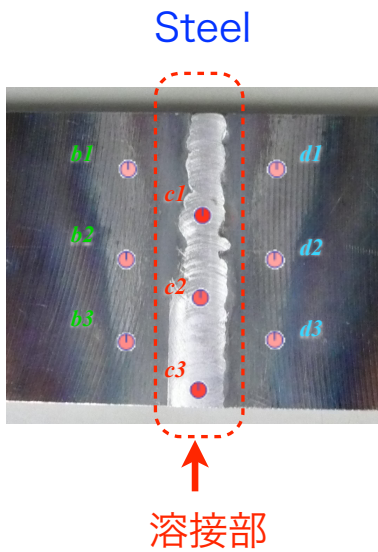
- 小さなスポットを大強度で測定

SANS patterns



溶接鉄の部位ごとの散乱強度の違い

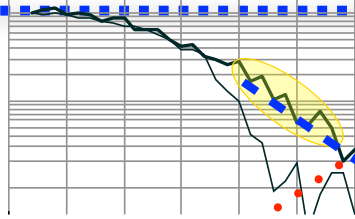
4.4~6.2Å



Resolving overlap, under development

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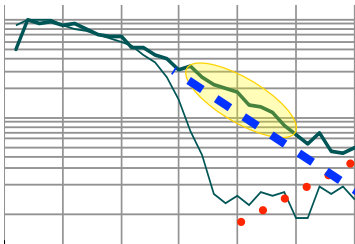
3.76 ~
4.39 Å



となりのピンホールからの影響
は少ない

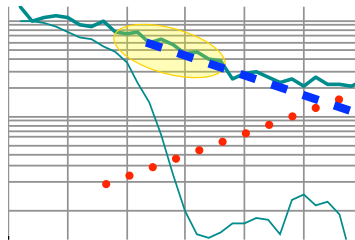
Q

4.56 ~
5.28 Å



Q

5.46 ~
6.18 Å



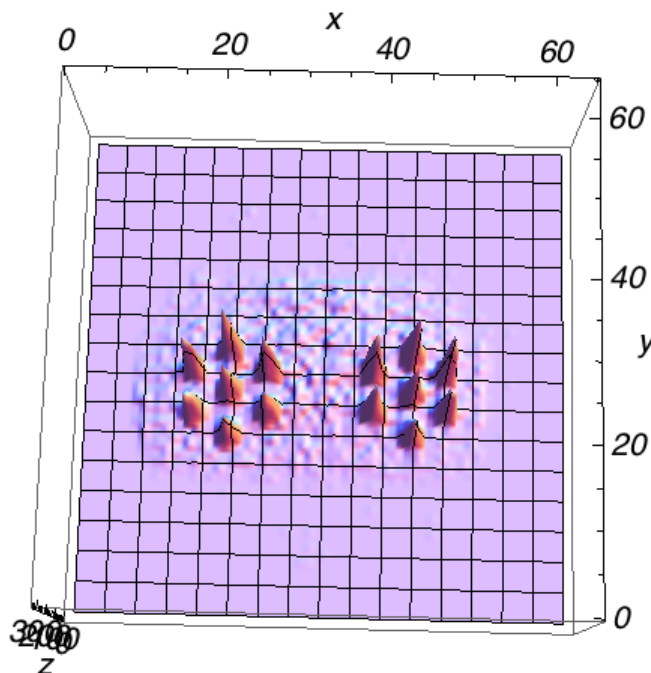
Q

TOFだから
出来る技

1mm ϕ Pinhole@Hokkaido Univ.

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Direct beam



Techniques for compact neutron sources

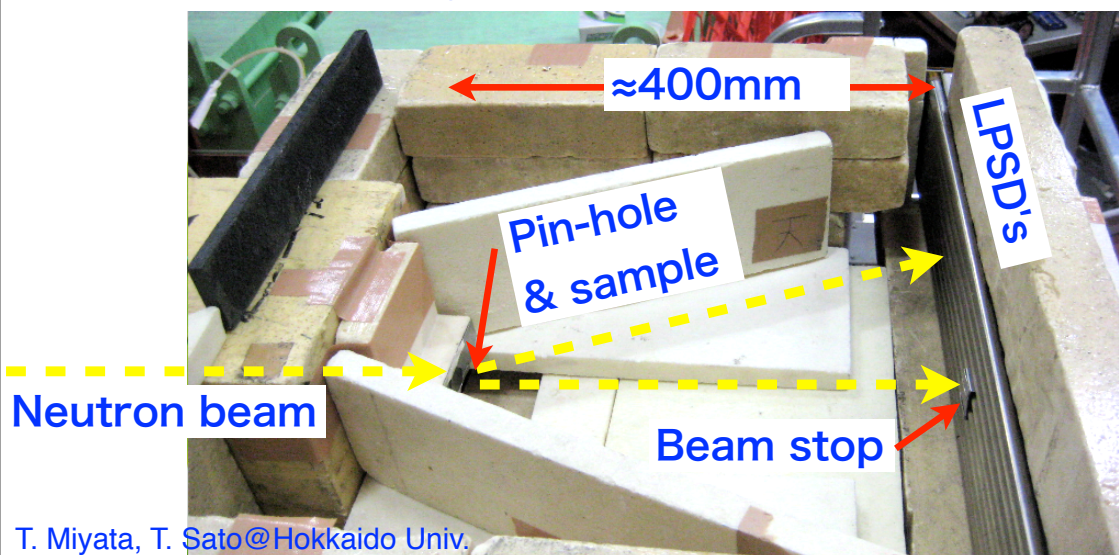
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Intermediate-angle scattering instrument @HU Linac

Intermediate angle scattering instrument HU linac

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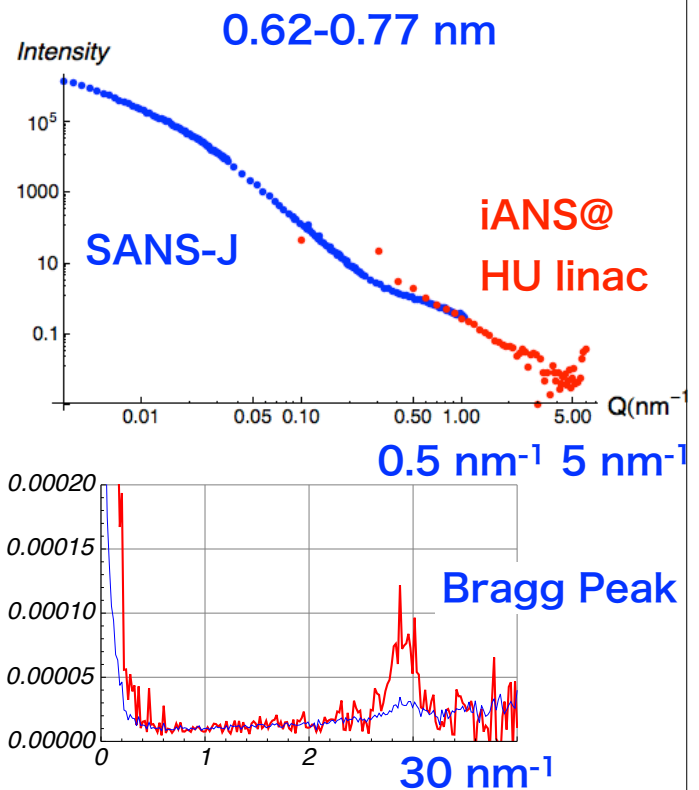
- Very low angular-resolution
= **highly efficient** at an intermediate-q range
- Large sample size; up to 20 mm
- Reasonable Q-range; $0.05 \leq Q \leq 2 \text{ \AA}^{-1}$



Test experiment using iANS@HU Linac

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- Steel sample "RSO414"
- Measuring time \approx 1 hr
- 1 kW beam power!
- Enough for nanoscopic structure study of alloy samples



まとめ

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まとめ

- mfSANS@mfSANSのphase Iが完成した。
 - 高い散乱強度の試料なら測定可能
 - nmスケールの高いQ領域の測定に向いている。
- 今後の性能向上が必要
 - 新型モノクロメータの高性能化
 - 検出器の高性能化 (MSGC)
 - 集束ミラーの改良が出来れば散乱強度が弱いものも
- mfSANS@J-PARCに向けて
 - 変形Kirkpatrick-Baez型を開発中
- 北大でも結構測定出来る
 - 1mm scanning SANSで測定、解析中
 - 0.02 \AA^{-1} - 5 \AA^{-1} なら測定可能。